1500 Watt Mosorb[™] Zener Transient Voltage Suppressors

Unidirectional*

Mosorb devices are designed to protect voltage sensitive components from high voltage, high–energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. These devices are ON Semiconductor's exclusive, cost-effective, highly reliable Surmetic[™] axial leaded package and are ideally-suited for use in communication systems, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications, to protect CMOS, MOS and Bipolar integrated circuits.

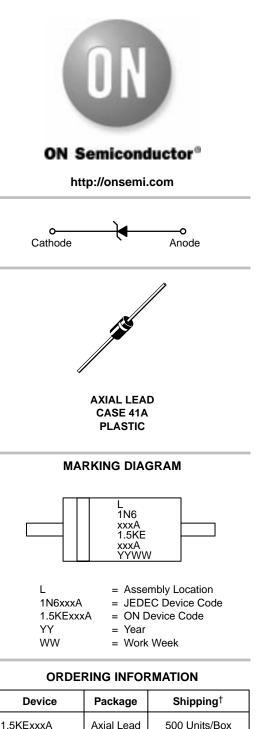
Features

- Working Peak Reverse Voltage Range 5.8 V to 214 V
- Peak Power 1500 Watts @ 1 ms
- ESD Rating of Class 3 (>16 kV) per Human Body Model
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage $< 5 \mu A$ Above 10 V
- UL 497B for Isolated Loop Circuit Protection
- Response Time is Typically < 1 ns
- These devices are manufactured with a Pb–Free external lead finish only*

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic **FINISH:** All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16 in from the case for 10 seconds POLARITY: Cathode indicated by polarity band MOUNTING POSITION: Any



Device	Package	Shipping [†]		
1.5KExxxA	Axial Lead	500 Units/Box		
1.5KExxxARL4	Axial Lead	1500/Tape & Reel		
1N6xxxA	Axial Lead	500 Units/Box		
1N6xxxARL4*	Axial Lead	1500/Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*1N6302A Not Available in 1500/Tape & Reel

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ $T_L \le 25^{\circ}C$	P _{PK}	1500	W
Steady State Power Dissipation @ $T_L \le 75^{\circ}$ C, Lead Length = 3/8 in	P _D	5.0	W
Derated above $T_L = 75^{\circ}C$		20	mW/°C
Thermal Resistance, Junction-to-Lead	$R_{ ext{ heta}JL}$	20	°C/W
Forward Surge Current (Note 2) @ $T_A = 25^{\circ}C$	I _{FSM}	200	А
Operating and Storage Temperature Range	T _J , T _{stg}	– 65 to +175	°C

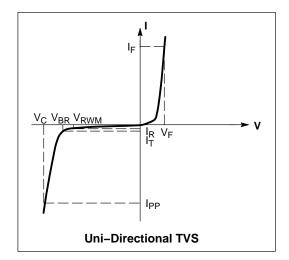
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Nonrepetitive current pulse per Figure 5 and derated above $T_A = 25^{\circ}C$ per Figure 2. 2. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

*Please see 1.5KE6.8CA to 1.5KE250CA for Bidirectional Devices

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted, V_F = 3.5 V Max., I_F (Note 3) = 100 A)

Symbol	Parameter			
I _{PP}	Maximum Reverse Peak Pulse Current			
V _C	Clamping Voltage @ IPP			
V _{RWM}	Working Peak Reverse Voltage			
I _R	Maximum Reverse Leakage Current @ V _{RWM}			
V _{BR}	Breakdown Voltage @ I _T			
Ι _Τ	Test Current			
ΘV_{BR}	Maximum Temperature Coefficient of VBR			
١ _F	Forward Current			
V _F	Forward Voltage @ I _F			



			I _R @ V _{RWM}	Breakdown Voltage			V _C @ I _{PP} (Note 7)			
	JEDEC Device			V _{BR} (Note 6) (Volts)		@ կ	v _c	I _{PP}	ΘV _{BR}	
Device	(Note 4)	(Volts)	(μ A)	Min	Nom	Max	(mA)	(Volts)	(A)	(%/°C)
1.5KE6.8A	1N6267A	5.8	1000	6.45	6.8	7.14	10	10.5	143	0.057
1.5KE7.5A	1N6268A	6.4	500	7.13	7.5	7.88	10	11.3	132	0.061
1.5KE8.2A	1N6269A	7.02	200	7.79	8.2	8.61	10	12.1	124	0.065
1.5KE9.1A	1N6270A	7.78	50	8.65	9.1	9.55	1	13.4	112	0.068
1.5KE10A	1N6271A	8.55	10	9.5	10	10.5	1	14.5	103	0.073
1.5KE11A	1N6272A	9.4	5	10.5	11	11.6	1	15.6	96	0.075
1.5KE12A	1N6273A	10.2	5	11.4	12	12.6	1	16.7	90	0.078
1.5KE13A	1N6274A	11.1	5	12.4	13	13.7	1	18.2	82	0.081
1.5KE15A	1N6275A	12.8	5	14.3	15	15.8	1	21.2	71	0.084
1.5KE16A	1N6276A	13.6	5	15.2	16	16.8	1	22.5	67	0.086
1.5KE18A	1N6277A	15.3	5	17.1	18	18.9	1	25.2	59.5	0.088
1.5KE20A	1N6278A	17.1	5	19	20	21	1	27.7	54	0.09
1.5KE22A	1N6279A	18.8	5	20.9	22	23.1	1	30.6	49	0.092
1.5KE24A	1N6280A	20.5	5	22.8	24	25.2	1	33.2	45	0.094
1.5KE27A	1N6281A	23.1	5	25.7	27	28.4	1	37.5	40	0.096
1.5KE30A	1N6282A	25.6	5	28.5	30	31.5	1	41.4	36	0.097
1.5KE33A	1N6283A	28.2	5	31.4	33	34.7	1	45.7	33	0.098
1.5KE36A	1N6284A	30.8	5	34.2	36	37.8	1	49.9	30	0.099
1.5KE39A	1N6285A	33.3	5	37.1	39	41	1	53.9	28	0.1
1.5KE43A	1N6286A	36.8	5	40.9	43	45.2	1	59.3	25.3	0.101
1.5KE47A	1N6287A	40.2	5	44.7	47	49.4	1	64.8	23.2	0.101
1.5KE51A	1N6288A	43.6	5	48.5	51	53.6	1	70.1	21.4	0.102
1.5KE56A	1N6289	47.8	5	53.2	56	58.8	1	77	19.5	0.103
1.5KE62A	1N6290A	53	5	58.9	62	65.1	1	85	17.7	0.104
1.5KE68A	1N6291A	58.1	5	64.6	68	71.4	1	92	16.3	0.104
1.5KE75A	1N6292A	64.1	5	71.3	75	78.8	1	103	14.6	0.105
1.5KE82A	1N6293A	70.1	5	77.9	82	86.1	1	113	13.3	0.105
1.5KE91A	1N6294A	77.8	5	86.5	91	95.5	1	125	12	0.106
1.5KE100A	1N6295A	85.5	5	95	100	105	1	137	11	0.106
1.5KE110A	1N6296A	94	5	105	110	116	1	152	9.9	0.107
1.5KE120A	1N6297A	102	5	114	120	126	1	165	9.1	0.107
1.5KE130A	1N6298A	111	5	124	130	137	1	179	8.4	0.107
1.5KE150A	1N6299A	128	5	143	150	158	1	207	7.2	0.108
1.5KE160A	1N6300A	136	5	152	160	168	1	219	6.8	0.108
1.5KE170A	1N6301A	145	5	162	170	179	1	234	6.4	0.108
1.5KE180A	1N6302A*	154	5	171	180	189	1	246	6.1	0.108
1.5KE200A	1N6303A	171	5	190	200	210	1	274	5.5	0.108
1.5KE220A		185	5	209	220	231	1	328	4.6	0.109
1.5KE250A		214	5	237	250	263	1	344	5	0.109

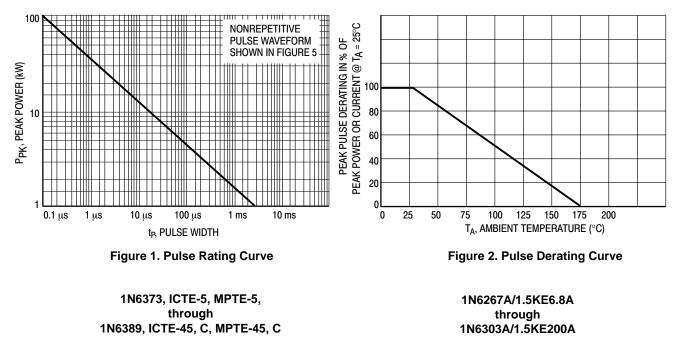
ELECTRICAL CHARACTERISTICS (T _A = 25°C unless otherwise noted, V _F = 3.5 V Max. @ I _F (Note 3) = 100 A)

Devices listed in bold, italic are ON Semiconductor Preferred devices. Preferred devices are recommended choices for future use and best overall value.

1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.
Indicates JEDEC registered data

A transient suppressor is normally selected according to the maximum working peak reverse voltage (V_{RWM}), which should be equal to or greater than the dc or continuous peak operating voltage level.

6. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C 7. Surge current waveform per Figure 5 and derate per Figures 1 and 2. *Not Available in the 1500/Tape & Reel



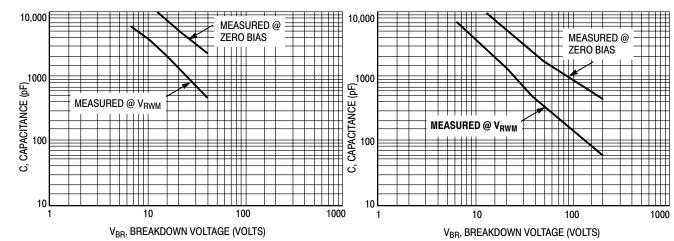
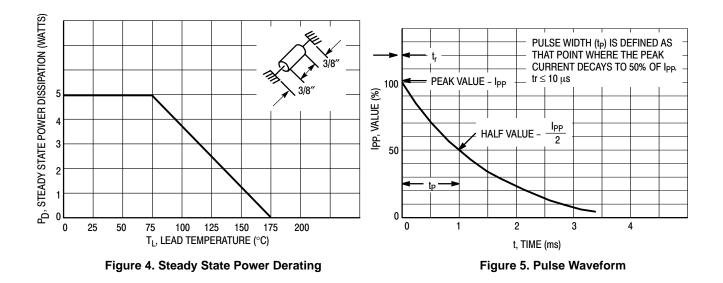


Figure 3. Capacitance versus Breakdown Voltage



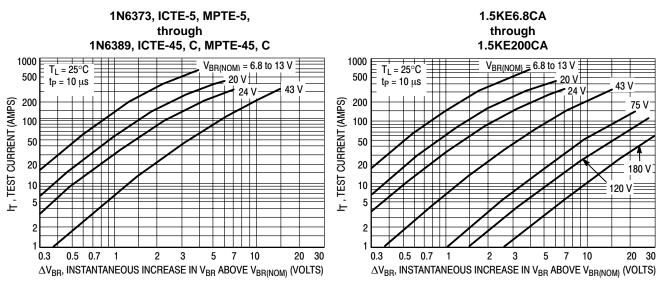
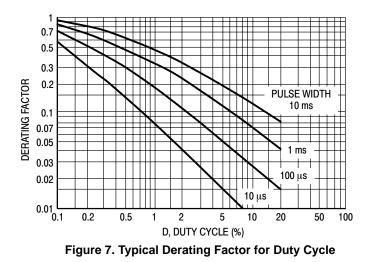


Figure 6. Dynamic Impedance



APPLICATION NOTES

RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitance effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 8.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 9. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. These devices have excellent response time, typically in the picosecond range and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper circuit layout, minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by Z_{in} is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

DUTY CYCLE DERATING

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 7. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 7 appear to be in error as the 10 ms pulse has a higher derating factor than the 10 μ s pulse. However, when the derating factor for a given pulse of Figure 7 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

Zin LOAD Vin Vı O Vin (TRANSIENT) OVERSHOOT DUE TO v ν INDUCTIVE EFFECTS Vin (TRANSIENT) ٧L Vı t_D = TIME DELAY DUE TO CAPACITIVE EFFECT Figure 8. Figure 9.

TYPICAL PROTECTION CIRCUIT



The entire series has *Underwriters Laboratory Recognition* for the classification of protectors (QVGV2) under the UL standard for safety 497B and File #116110. Many competitors only have one or two devices recognized or have recognition in a non-protective category. Some competitors have no recognition at all. With the UL497B recognition, our parts successfully passed several tests including Strike Voltage Breakdown test, Endurance Conditioning, Temperature test, Dielectric Voltage-Withstand test, Discharge test and several more.

Whereas, some competitors have only passed a flammability test for the package material, we have been recognized for much more to be included in their Protector category.

*Applies to 1.5KE6.8A, CA thru 1.5KE250A, CA

CLIPPER BIDIRECTIONAL DEVICES

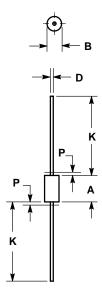
- Clipper-bidirectional devices are available in the 1.5KEXXA series and are designated with a "CA" suffix; for example, 1.5KE18CA. Contact your nearest ON Semiconductor representative.
- 2. Clipper-bidirectional part numbers are tested in both directions to electrical parameters in preceding table (except for V_F which does not apply).

3. The 1N6267A through 1N6303A series are JEDEC registered devices and the registration does not include a "CA" suffix. To order clipper-bidirectional devices one must add CA to the 1.5KE device title.

OUTLINE DIMENSIONS

MOSORB CASE 41A-04

ISSUE D



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. LEAD FINISH AND DIAMETER UNCONTROLLED IN DIMENSION P. 4. 041A-01 THRU 041A-03 OBSOLETE, NEW STANDARD 041A-04.

	INC	HES	MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	0.335	0.374	8.50	9.50		
В	0.189	0.209	4.80	5.30		
D	0.038	0.042	0.96	1.06		
K	1.000		25.40			
P		0.050		1.27		

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